TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type (U-MOS -H)

TPCC8001-H

High-Efficiency DC-DC Converter Applications Notebook PC Applications Portable Equipment Applications

- Small footprint due to a small and thin package
- High-speed switching
- Small gate charge: Q_{SW} = 7.1 nC (typ.)
- Low drain-source ON-resistance:

 $R_{DS (ON)} = 7.6 \text{ m}\Omega \text{ (typ.)} \text{ (V}_{GS} = 4.5 \text{ V)}$

- High forward transfer admittance: $|Y_{fS}| = 65 \text{ S (typ.)}$
- Low leakage current: $I_{DSS} = 10 \mu A \text{ (max) (V}_{DS} = 30 \text{ V)}$
- Enhancement mode: $V_{th} = 1.5$ to 2.5 V ($V_{DS} = 10$ V, $I_D = 1$ mA)

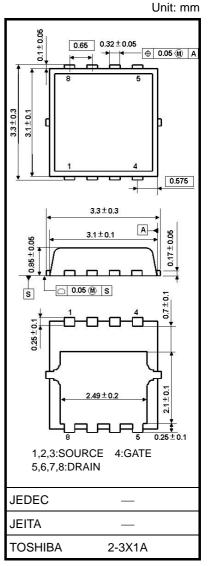
Absolute Maximum Ratings (Ta = 25°C)

| Characte | eristic | Symbol | Rating | Unit |
|--------------------------|-----------------------------|------------------|-----------------------|------|
| Drain-source voltage | | V_{DSS} | 30 | V |
| Drain-gate voltage (R | $GS = 20 \text{ k}\Omega$ | V_{DGR} | 30 | V |
| Gate-source voltage | | V_{GSS} | ±20 | V |
| Drain current | DC (Note 1) | I _D | 22 | Α |
| Diam current | Pulsed (Note 1) | I _{DP} | 22 66 30 1.9 | A |
| Drain power dissipati | on (Tc = 25) | P_{D} | 30 | W |
| Drain power dissipation | on (t = 10 s) (Note 2a) | P_{D} | 1.9 | W |
| Drain power dissipati | on (t = 10 s) (Note 2b) | P _D | 0.7 | W |
| Single-pulse avalance | ne energy (Note 3) | E _{AS} | 126 | mJ |
| Avalanche current | | I _{AR} | 22 | Α |
| Repetitive avalanche (To | energy c = 25) (Note 4) | E _{AR} | 2.1 | mJ |
| Channel temperature | | T _{ch} | 150 | °C |
| Storage temperature | range | T _{stg} | -55 to 150 | °C |

Note: For Notes 1 to 4, refer to the next page.

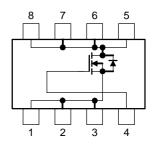
Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

This transistor is an electrostatic-sensitive device. Handle with care.



Weight: 0.02 g (typ.)

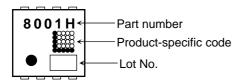
Circuit Configuration



Thermal Characteristics

| Characteristic | Symbol | Max | Unit |
|---|------------------------|-----|------|
| Thermal resistance, channel to case (Tc = 25) | R _{th (ch-c)} | 4.2 | °C/W |
| Thermal resistance, channel to ambient $(t = 10 \text{ s})$ (Note 2a) | R _{th (ch-a)} | 66 | °C/W |
| Thermal resistance, channel to ambient (t = 10 s) (Note 2b) | R _{th (ch-a)} | 180 | °C/W |

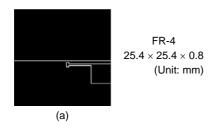
Marking (Note 5)

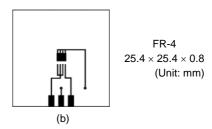


Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: (a) Device mounted on a glass-epoxy board (a)

(b) Device mounted on a glass-epoxy board (b)





Note 3: $V_{DD} = 24~V,~T_{Ch} = 25^{\circ}C$ (initial), $L = 200~\mu H,~R_G = 25~\Omega,~I_{AR} = 22~A$

Note 4: Repetitive rating: pulse width limited by maximum channel temperature

Note 5: * Weekly code: (Three digits)



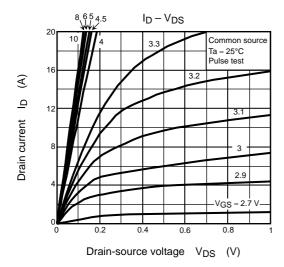
Electrical Characteristics (Ta = 25°C)

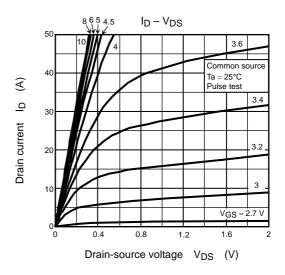
| Ch | aracteristic | Symbol | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------|--|---|---|-----|--|--------------|------|
| Gate leakage cur | rent | I _{GSS} | $V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$ | _ | _ | ±100 | nA |
| Drain cutoff curre | nt | I _{DSS} | V _{DS} = 30 V, V _{GS} = 0 V | | _ | 10 | μА |
| Drain agurag bro | okdowa voltogo | V (BR) DSS | $I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$ | 30 | - + 100 - 10 30 15 - 2.5 - 7.6 10.6 - 5.5 8.3 33 65 1900 2500 - 110 170 - 400 1.0 1.5 - 2.8 9.8 5.9 - 27 | V | |
| Drain-source breakdown voltage | | V (BR) DSX | $I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$ | 15 | _ | _ | V |
| Gate threshold vo | oltage | V _{th} | $V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$ | 1.5 | _ | 2.5 | V |
| Drain-source ON | Drain aguras ON registance | | $V_{GS} = 4.5 \text{ V}, I_D = 11 \text{ A}$ | _ | 7.6 | 10.6 | mO. |
| Dialii-source Oiv | -resistance | NDS (ON) | V _{GS} = 10 V, I _D = 11 A | _ | 5.5 | 8.3 | mΩ |
| Forward transfer | admittance | Y _{fs} | V _{DS} = 10 V, I _D = 11 A | 33 | 65 | _ | S |
| Input capacitance |) | C _{iss} | | _ | 1900 | 2500 | |
| Reverse transfer capacitance | | C _{rss} | $V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$ | _ | 110 | 170 | pF |
| Output capacitance | | C _{oss} | | _ | 400 | _ | |
| Gate resistance | | rg | $V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 5 \text{ MHz}$ | _ | 1.0 | 1.5 | Ω |
| | Rise time | t _r | 10 V □ Ip = 11 A | _ | 2.8 | _ | |
| Switching time | $\begin{array}{c} V_{c}(BR) \ DSS & I_{D} = 10 \ mA, \ V_{GS} = 0 \ V \\ V_{c}(BR) \ DSS & I_{D} = 10 \ mA, \ V_{GS} = -20 \ V \\ V_{c}(BR) \ DSS & I_{D} = 10 \ mA, \ V_{GS} = -20 \ V \\ V_{c}(BR) \ DSS & I_{D} = 10 \ mA, \ V_{GS} = -20 \ V \\ V_{c}(BR) \ DSS & I_{D} = 10 \ mA, \ V_{GS} = -20 \ V \\ V_{c}(BR) \ DSS & I_{D} = 10 \ mA, \ V_{GS} = -20 \ V \\ V_{c}(BR) \ DSS & I_{D} = 10 \ mA, \ V_{GS} = -20 \ V \\ V_{c}(BR) \ DSS & I_{D} = 10 \ mA, \ V_{GS} = -20 \ V \\ V_{c}(BR) \ DSS & I_{D} = 10 \ MA, \ V_{GS} = 10 \ V, \ I_{D} = 11 \ A \\ V_{c}(BR) \ DSS & I_{D} = 10 \ MA, \ V_{GS} = 10 \ V, \ I_{D} = 11 \ A \\ V_{c}(BR) \ DSS & I_{D} = 10 \ V, \ V_{C}(BR) \ DSS & I_{D} = 10 \ V, \ V_{C}(BR) \ DSS & I_{D} = 10 \ V, \ V_{C}(BR) \ DSS & I_{D} = 10 \ V, \ V_{C}(BR) \ DSS & I_{D} = 10 \ V, \ V_{C}(BR) \ DSS & I_{D} = 10 \ V, \ V_{C}(BR) \ DSS & I_{D} = 10 \ V, \ I_{D} = 10 \$ | _ | 200 | | | | |
| Switching time | Fall time | t _f | RL = 13 | _ | 5.9 | 2.5 10.6 8.3 | ns |
| | Turn-off time | t _{off} | V _{DD} ≈ 15 V | _ | 27 | _ | |
| Total gate charge | • | V _{DD} ≈ 24 V, V _{GS} = 10 V, I _D = 22 A | | _ | | | |
| (gate-source plus | gate-drain) | Qg | $V_{DD} \approx 24 \text{ V}, V_{GS} = 5 \text{ V}, I_{D} = 22 \text{ A}$ | _ | 14.3 | | |
| Gate-source charge 1 | | Q _{gs1} | | _ | 6.8 | _ | nC |
| Gate-drain ("Miller") charge | | Q _{gd} | $V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 22 \text{ A}$ | _ | 4.3 | _ | |
| Gate switch charg | ge | $\begin{array}{c ccccccccccccccccccccccccccccccccccc$ | | _ | | | |

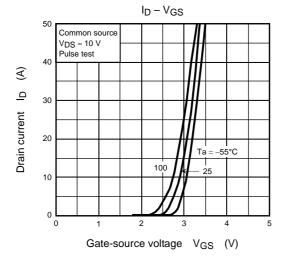
Source-Drain Ratings and Characteristics (Ta = 25°C)

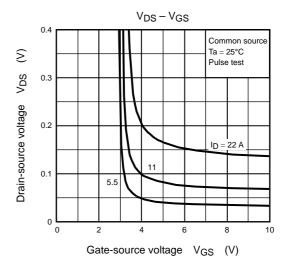
| Characteristic | | Symbol | Test Condition | Min | Тур. | Max | Unit | |
|-------------------------|-------|----------|------------------|---|------|-----|------|---|
| Drain reverse current | Pulse | (Note 1) | I _{DRP} | _ | _ | _ | 66 | Α |
| Forward voltage (diode) | | | V _{DSF} | $I_{DR} = 22 \text{ A}, V_{GS} = 0 \text{ V}$ | | _ | -1.2 | V |

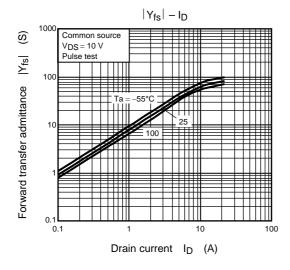
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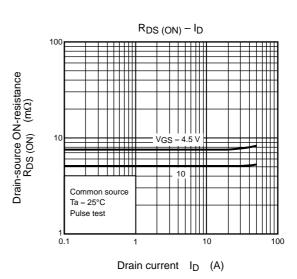




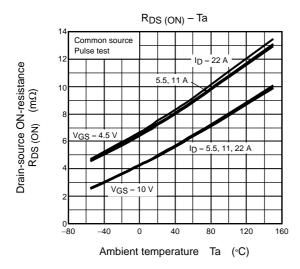


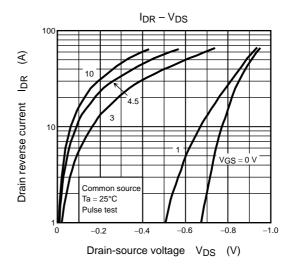


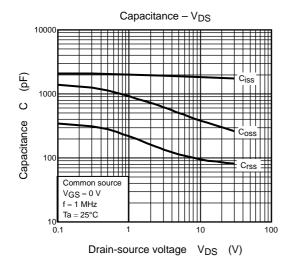


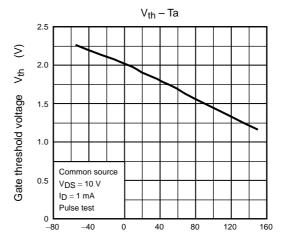


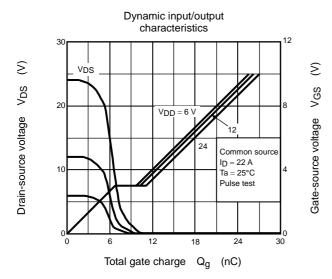
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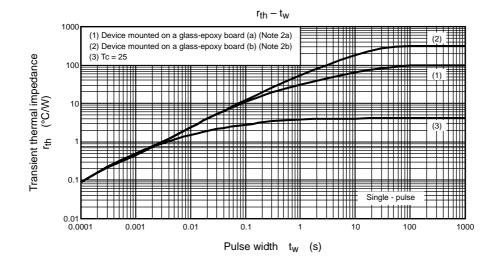


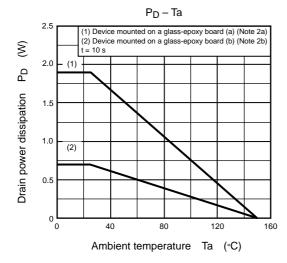


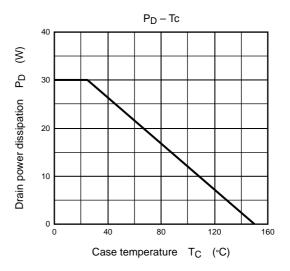


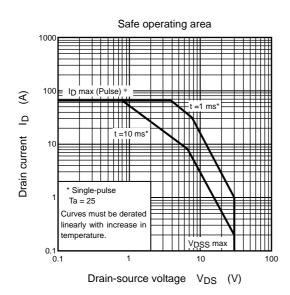


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